IN THE CLAIMS:

Please cancel claims 7-20 without prejudice or disclaimer as follows:

- 1. (Previously Presented) A semiconductor device having a heat spreader comprising a diamond-containing material having a thermal conductivity t, where 350≤t<1000 W/(m·K), the heat spreader being directly disposed entirely or partially on the reverse surface of the semiconductor device, wherein the diamond-containing material is a composite of a diamond layer and a ceramic layer or a mixture of diamond particles and ceramic particles, the ceramic layer or the ceramic particles comprising at least one of silicon carbide and aluminum nitride.
- 2. (Cancelled)
- 3. (Original) The semiconductor device according to Claim 1, wherein the heat spreader is directly disposed on a substrate for the semiconductor device.
- 4. (Original) The semiconductor device according to Claim 1, wherein the heat spreader has an irregular surface facing away from the semiconductor device.
- 5. (Previously Presented) A semiconductor package accommodating the semiconductor device having a heat spreader comprising a diamond-containing material having a thermal conductivity t, where 350≤t<1000 W/(m·K), the heat spreader being directly disposed entirely or partially on the reverse surface of the semiconductor device, wherein a metal heat sink or a metal radiating fin is bonded on a surface of the heat spreader facing away from the semiconductor device, and the diamond-containing material is a composite of a diamond layer and a ceramic layer or a mixture of diamond particles and ceramic particles, the ceramic layer or the ceramic particles comprising at least one of silicon carbide and aluminum nitride.
- 6. (Original) The semiconductor package according to Claim 5, wherein a polymer adhesive layer is used to bond the metal heat sink or the metal radiating fin on the

surface of the heat spreader, and cilia are formed on the surface of the heat spreader so that the polymer adhesive layer spreads over part of the cilia.

7-20. (Cancelled)